

General Description

- Trench Power MV MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications

Applications

- Synchronous Rectification in DC/DC and AC/DC Converters
- Industrial and Motor Drive applications

Product Summary

V_{DS}	40V
I_D (at $V_{GS}=10V$)	85A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 2.9m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 4.2m Ω

100% UIS Tested
100% Rg Tested

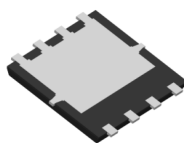


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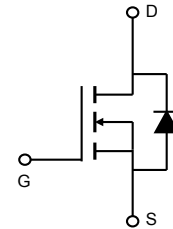
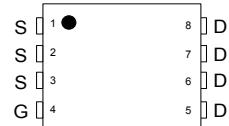
Top View



Bottom View



Top View



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AON6232A	DFN 5x6	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	85	A
Pulsed Drain Current ^C	I_{DM}	260	A
Continuous Drain Current	I_{DSM}	35	A
Avalanche Current ^C	I_{AS}	60	A
Avalanche energy $L=0.1\text{mH}$ ^C	E_{AS}	180	mJ
V_{DS} Spike	V_{SPIKE}	48	V
Power Dissipation ^B	P_D	113.5	W
Power Dissipation ^A	P_{DSM}	45.5	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	15	20	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.9	1.1	$^\circ\text{C/W}$

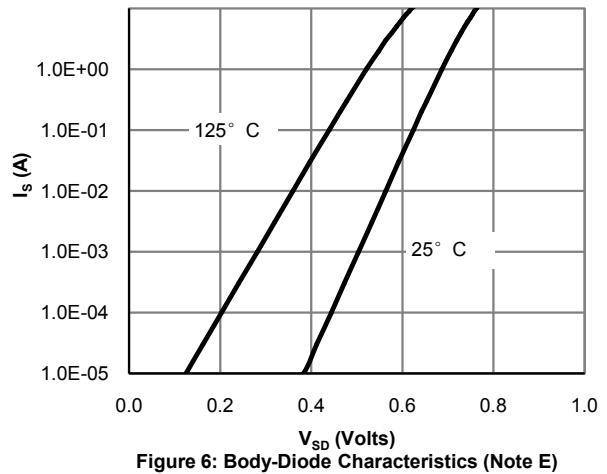
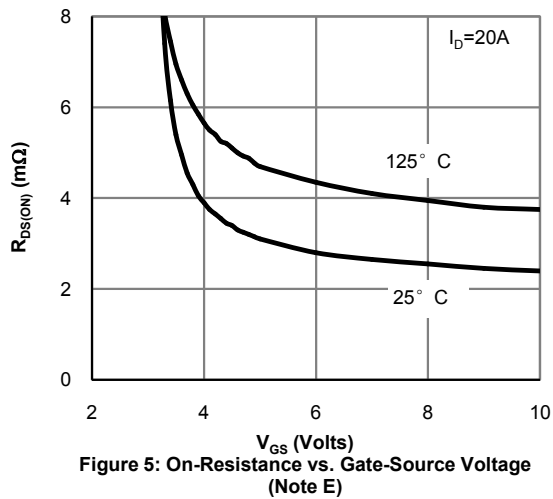
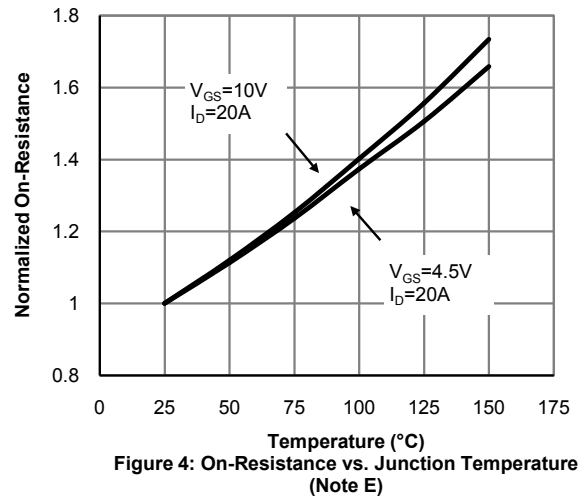
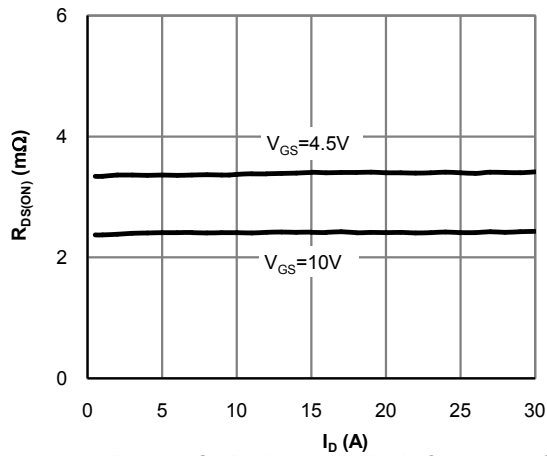
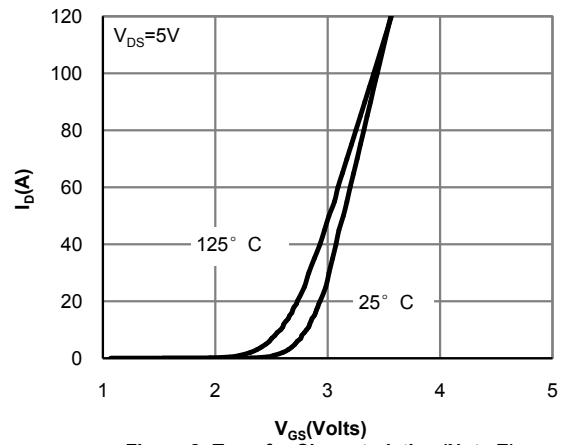
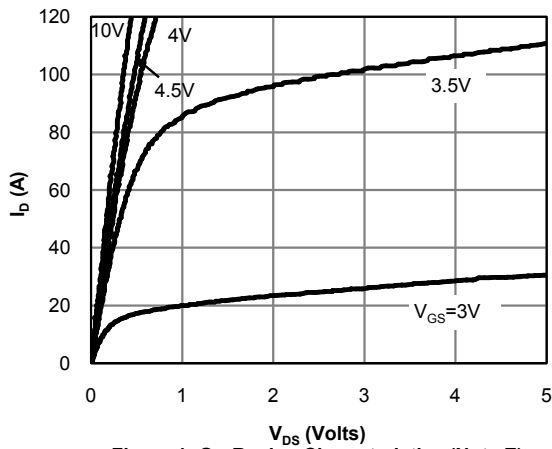
Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.4	1.9	2.5	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		2.4 3.75	2.9 4.55	mΩ
		V _{GS} =4.5V, I _D =20A		3.35	4.2	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		100		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.68	1	V
I _S	Maximum Body-Diode Continuous Current ^G				85	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, f=1MHz		3250		pF
C _{oss}	Output Capacitance			835		pF
C _{rss}	Reverse Transfer Capacitance			43		pF
R _g	Gate resistance	f=1MHz	0.4	0.85	1.3	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =20V, I _D =20A		42	60	nC
Q _{g(4.5V)}	Total Gate Charge			19	28	nC
Q _{gs}	Gate Source Charge			8		nC
Q _{gd}	Gate Drain Charge			5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =20V, R _L =1.0Ω, R _{GEN} =3Ω		10		ns
t _r	Turn-On Rise Time			3.5		ns
t _{D(off)}	Turn-Off DelayTime			32		ns
t _f	Turn-Off Fall Time			4		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=500A/μs		21		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=500A/μs		62		nC

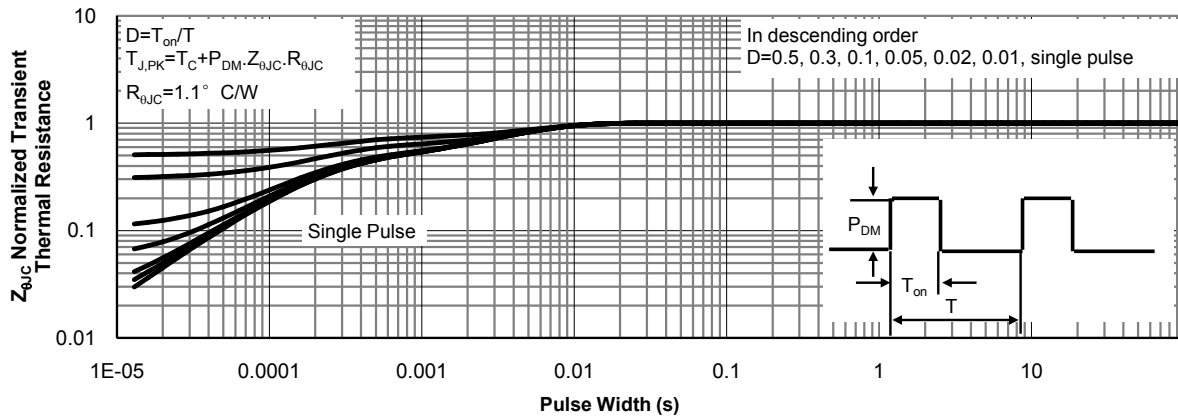
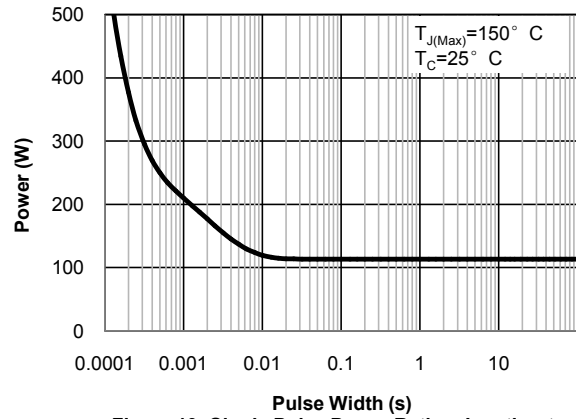
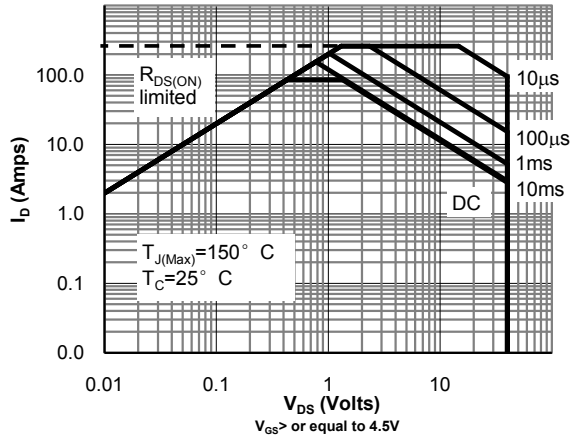
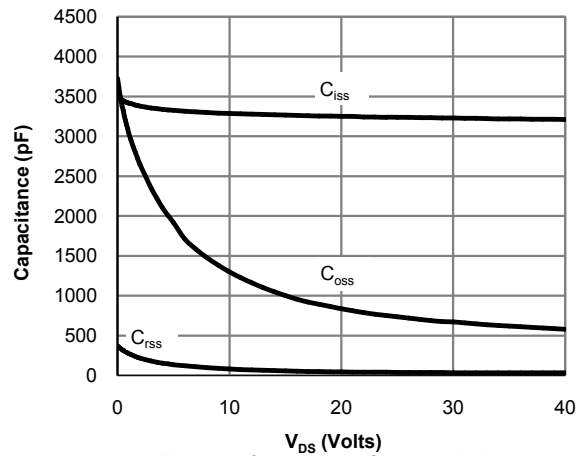
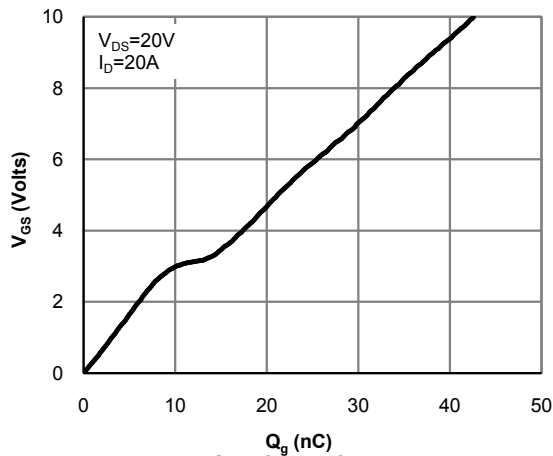
- A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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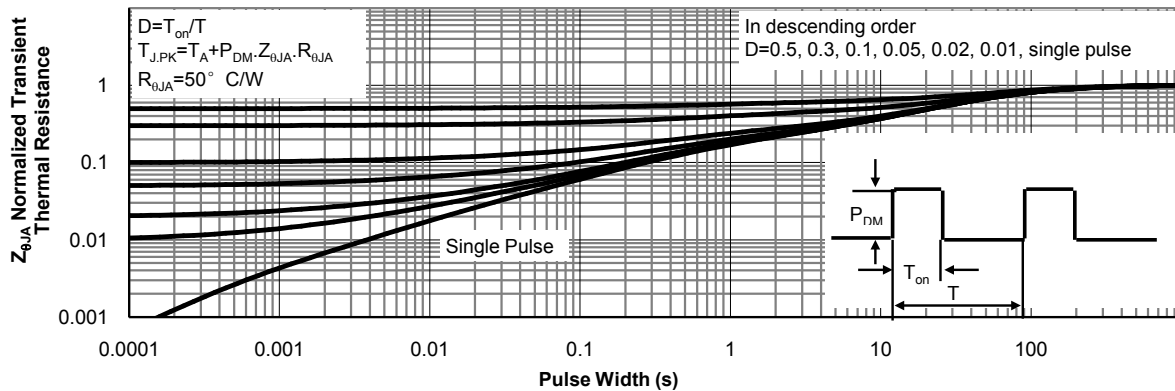
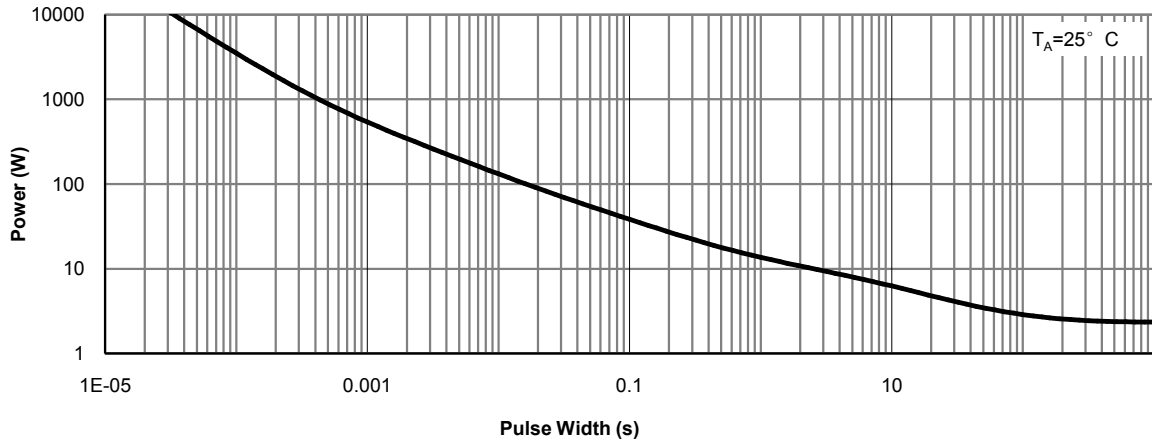
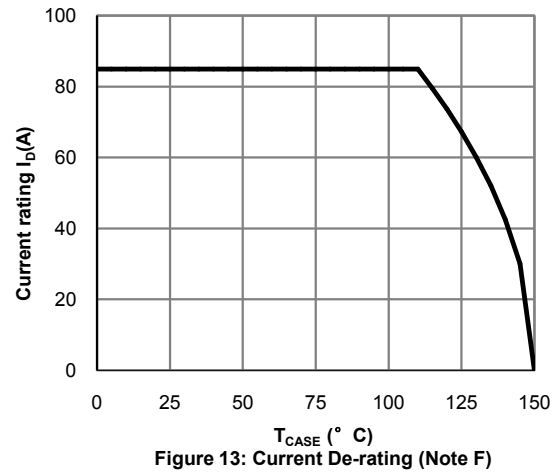
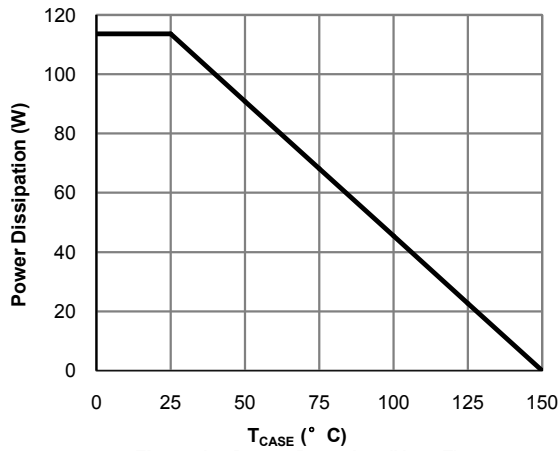
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



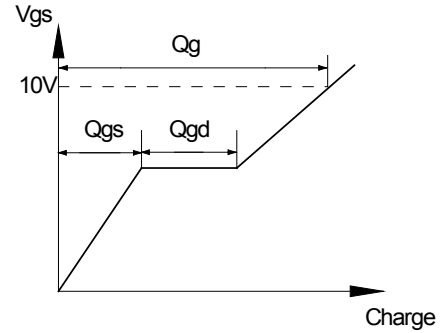
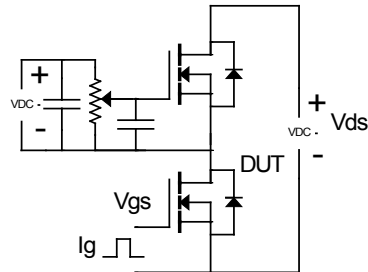
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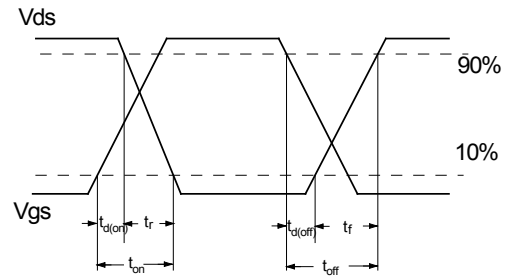
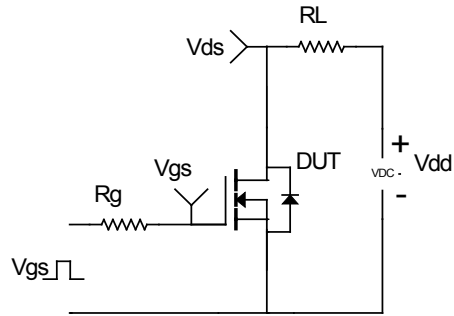
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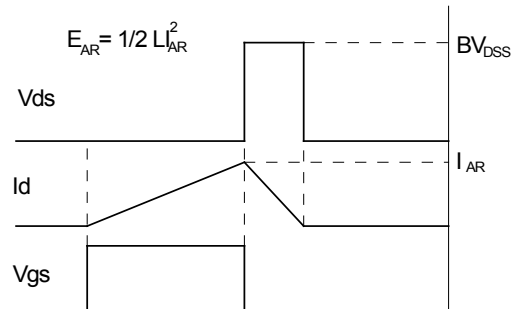
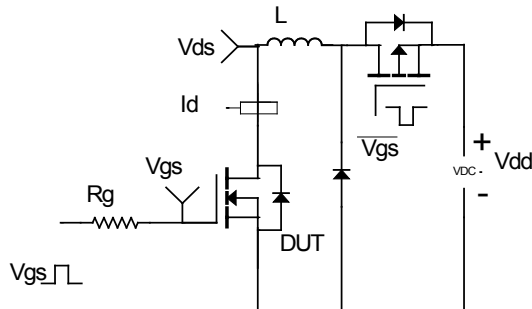
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

